

Fig.1(a)

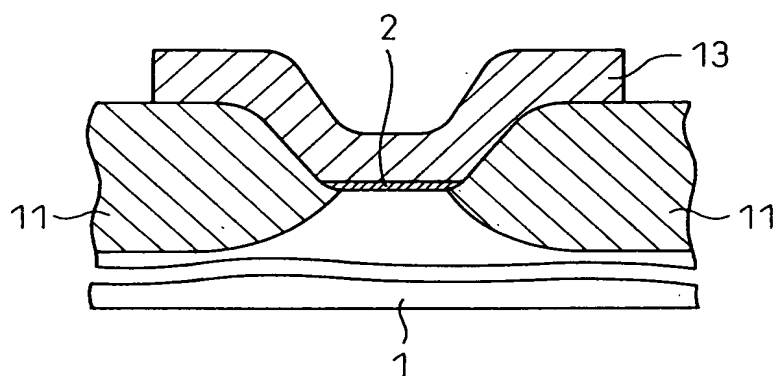


Fig.1(b)

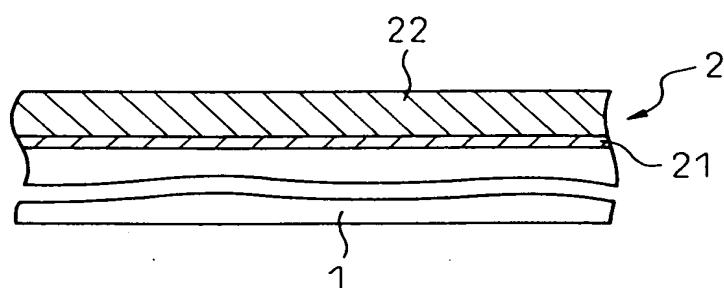


Fig.2

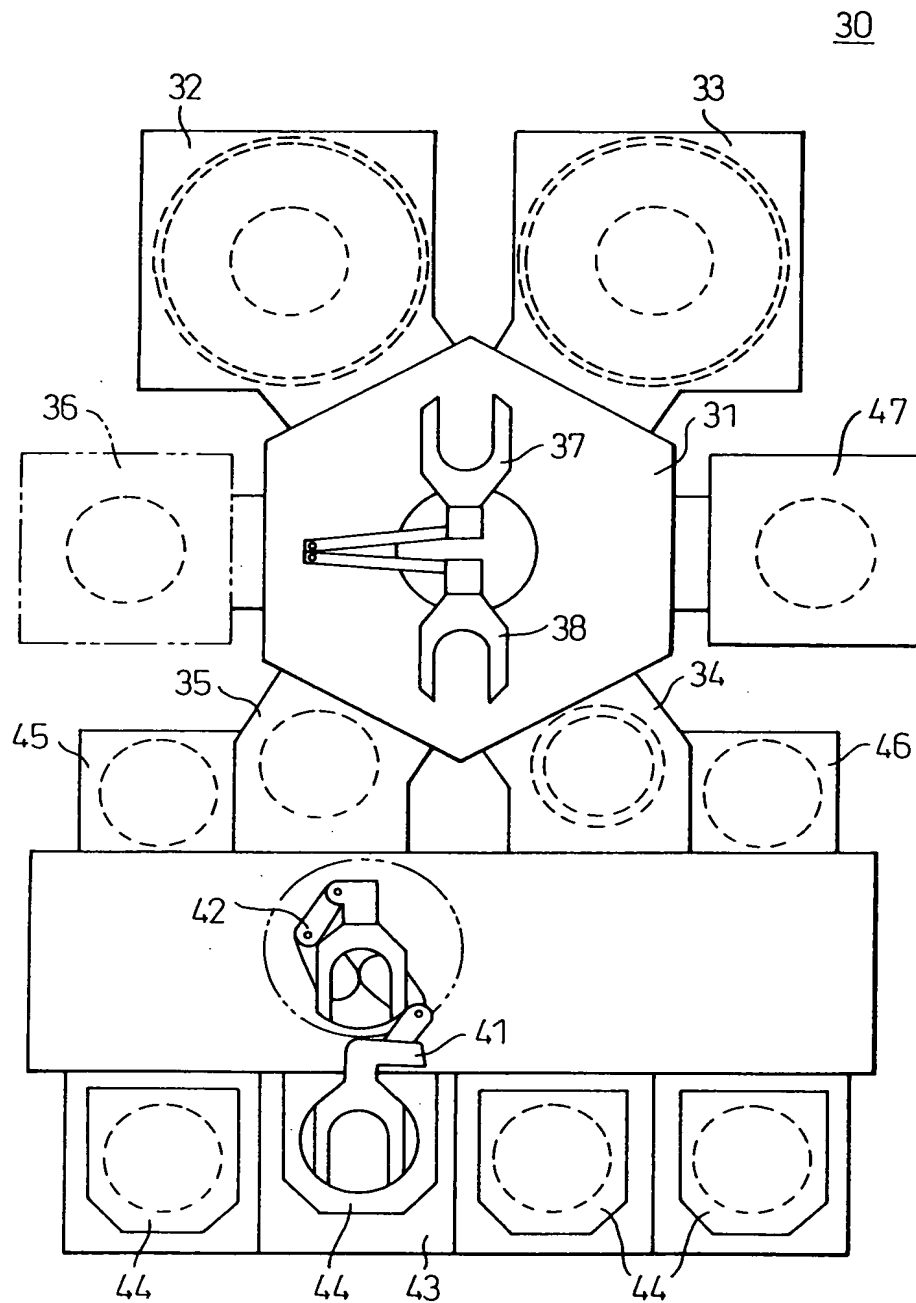


Fig. 3

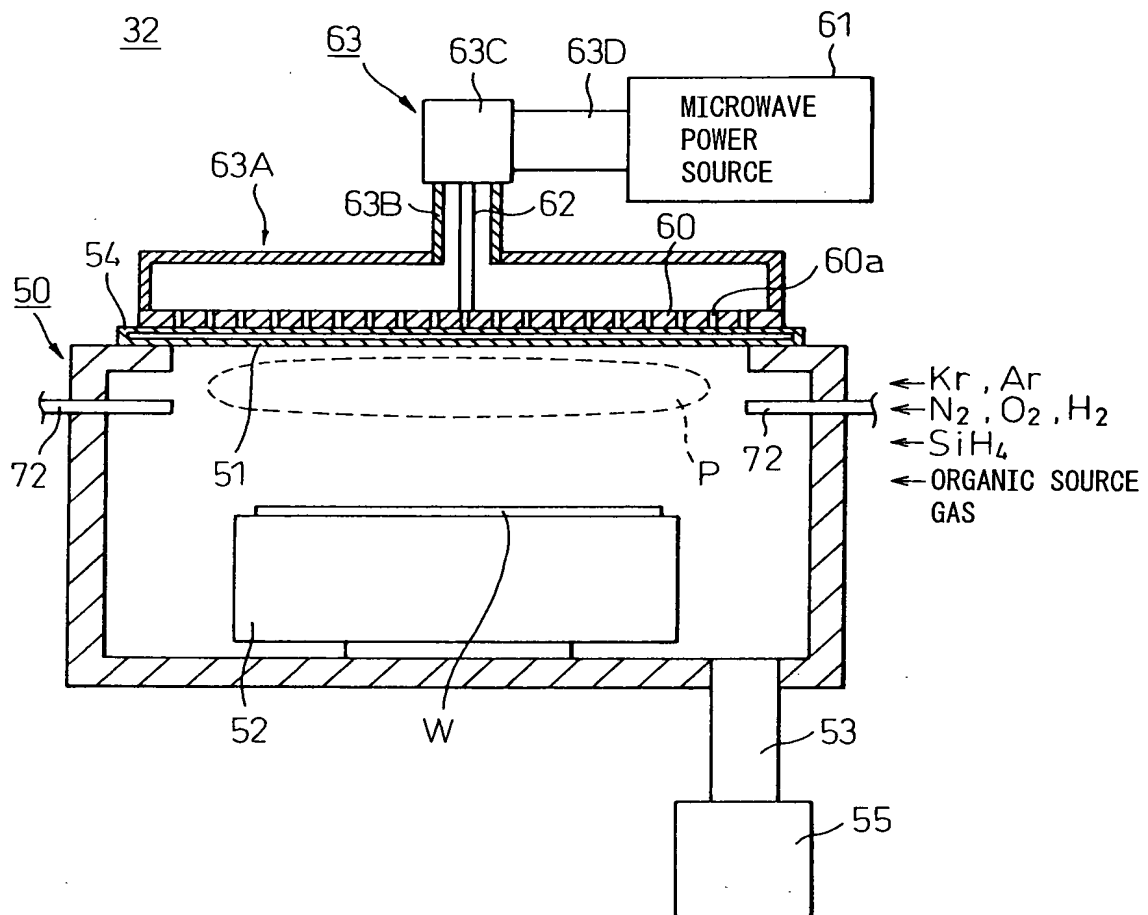


Fig.4

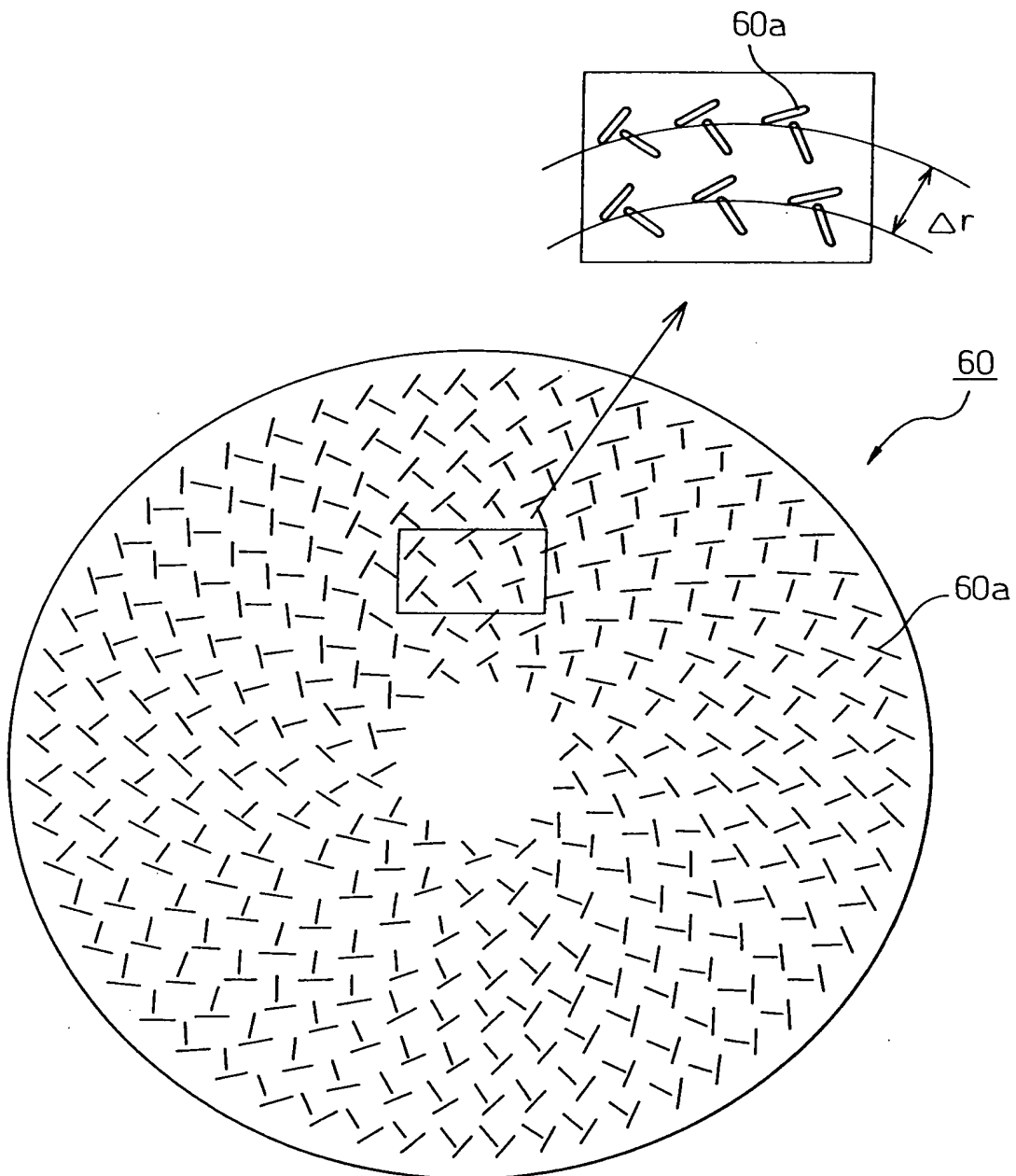


Fig. 5

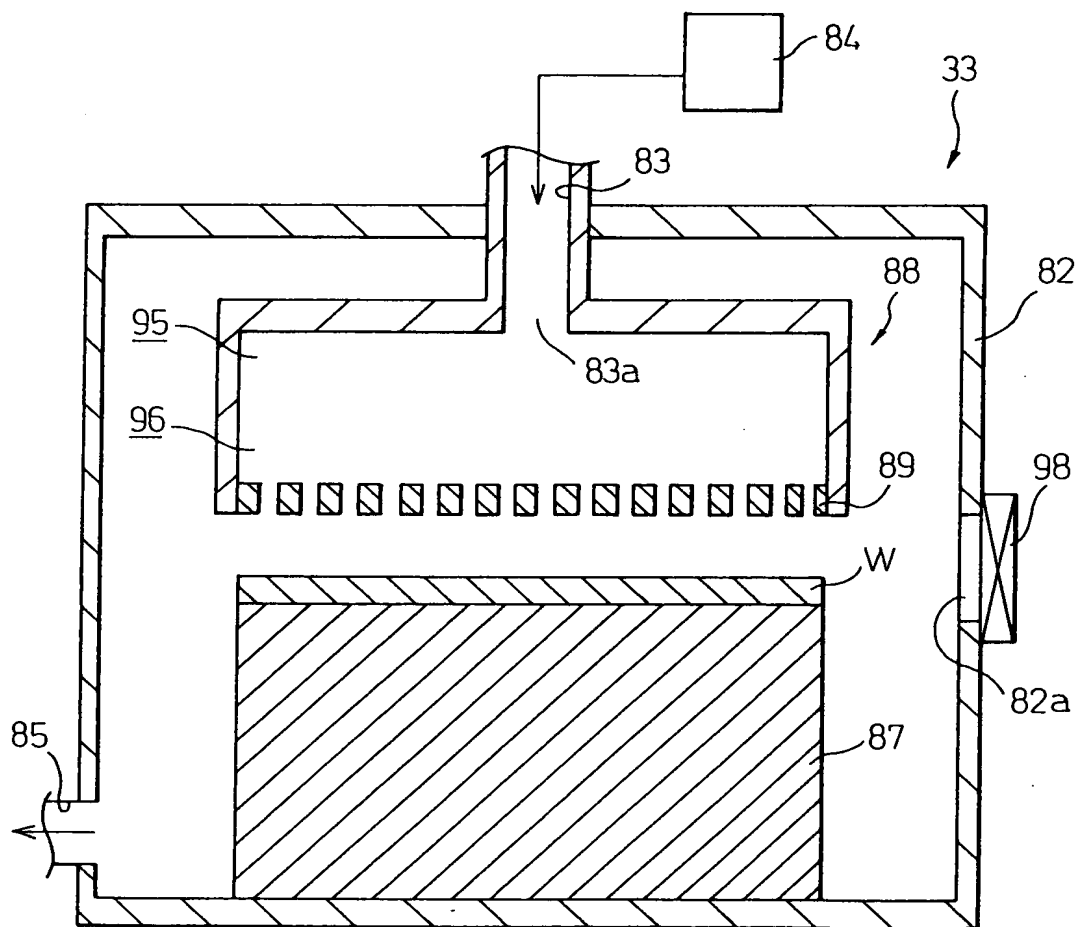


Fig. 6

FORMATION OF DEVICE ISOLATION 11 (FIELD OXIDE FILM, LOCOS, STI) (PRE-PROCESSING)



PRE-WASHING OF GATE INSULATING FILM (RCA WASHING)



FORMATION OF GATE INSULATING FILM 2

(
FORMATION OF UNDERLYING OXIDE FILM 21
↓
FORMATION OF CVD INSULATING FILM 22



FORMATION OF GATE ELECTRODE 13

Fig. 7(a)

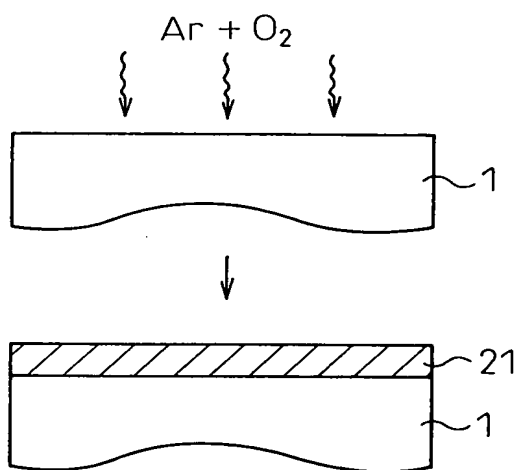


Fig. 7(b)

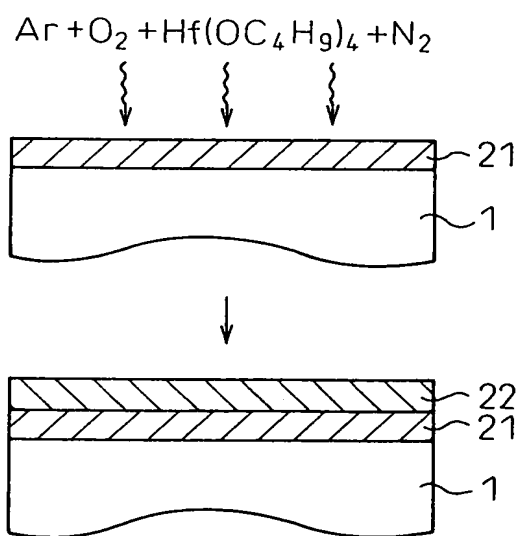


Fig.8

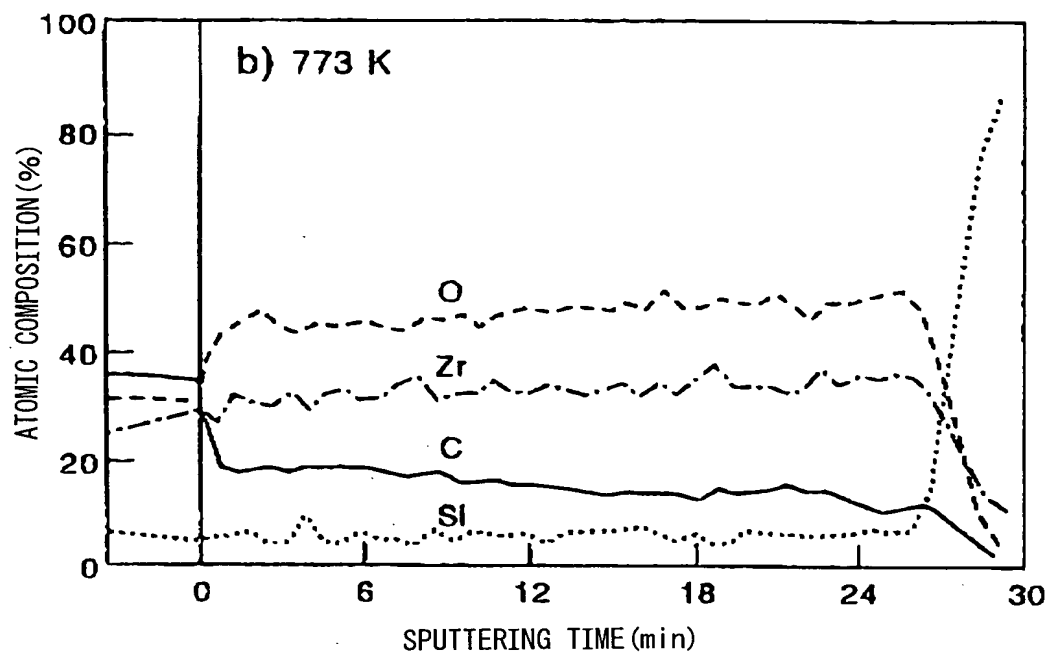


Fig.9

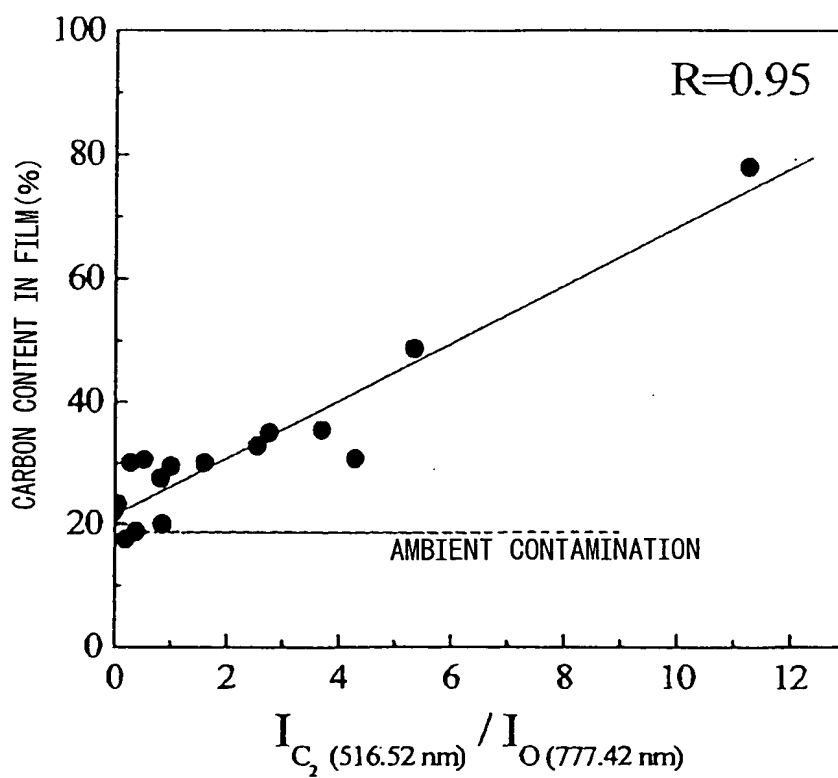


Fig.10(a)

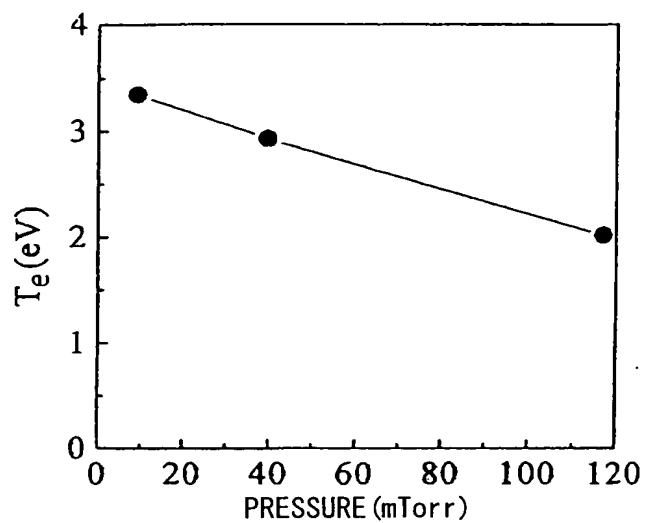


Fig.10(b)

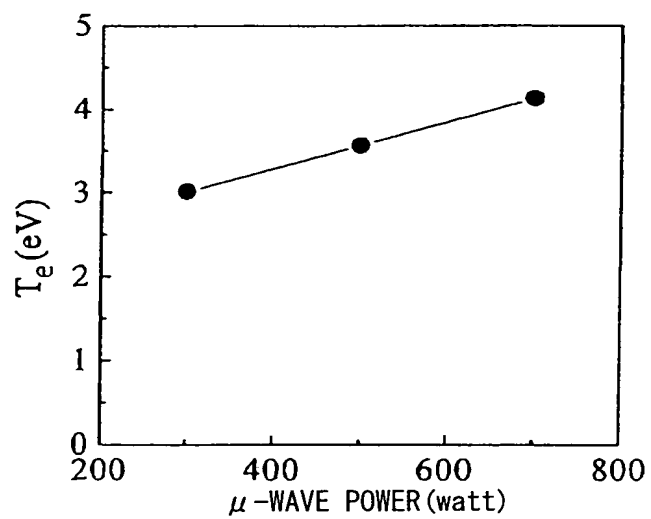


Fig.10(c)

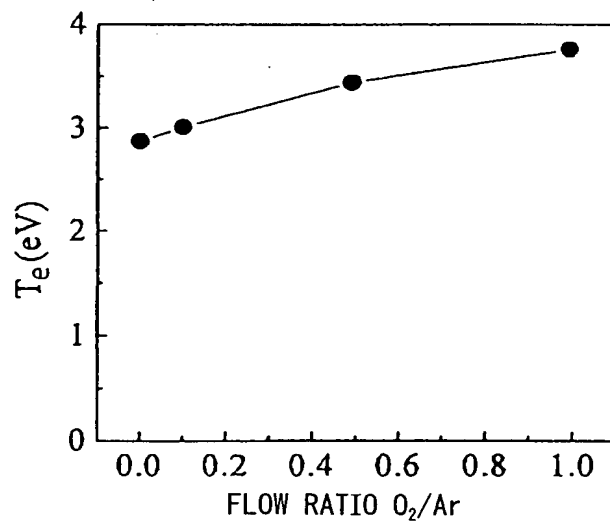


Fig.11

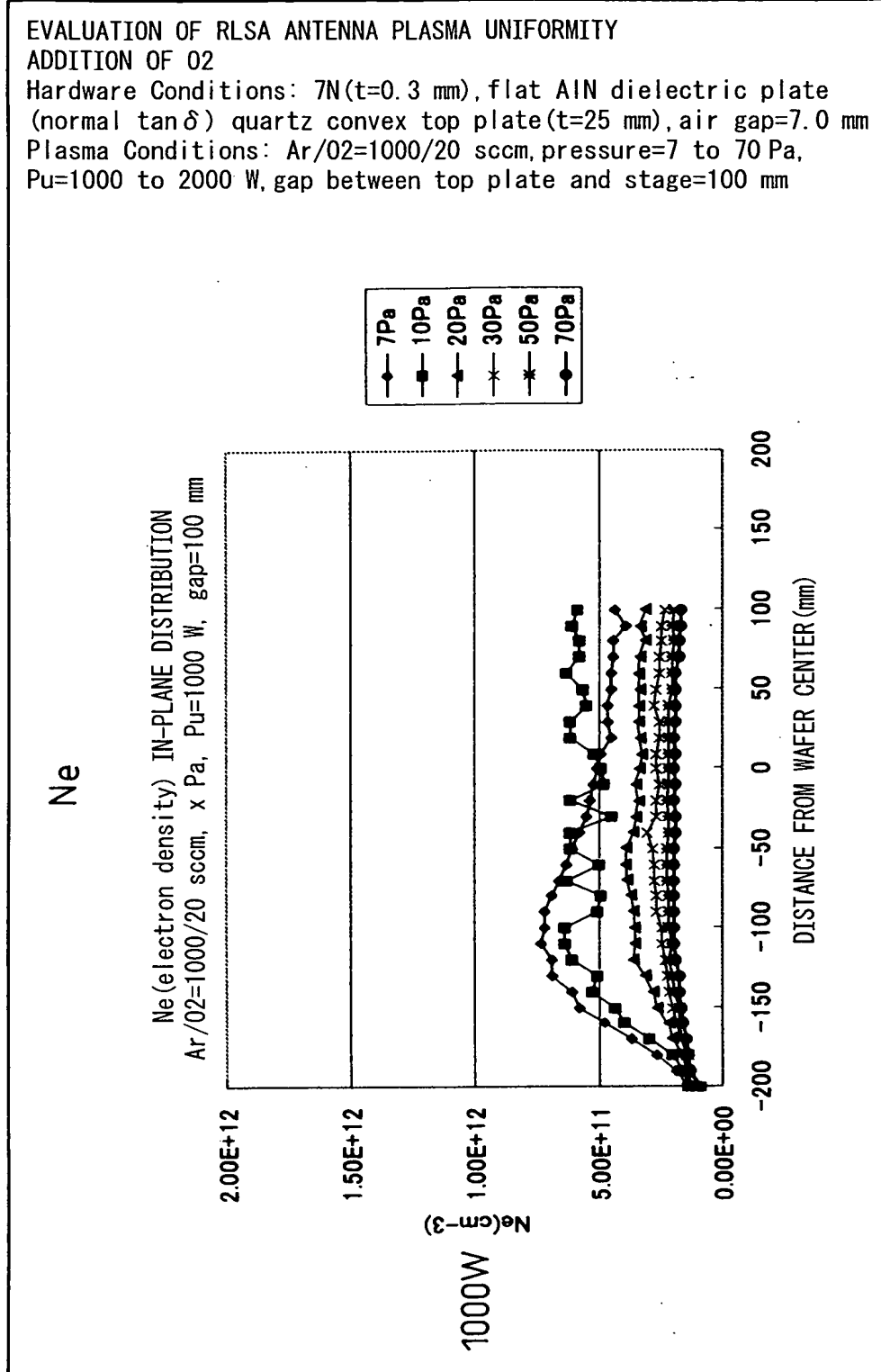


Fig.12

EVALUATION OF RLSA ANTENNA PLASMA UNIFORMITY ADDITION OF O₂

Hardware Conditions: 7N(t=0.3 mm), flat AlN dielectric plate (normal $\tan\delta$) quartz convex top plate(t=25 mm), air gap=7.0 mm
 Plasma Conditions: Ar/O₂=1000/20 sccm, pressure=7 to 70 Pa, Pu=1000 to 2000 W, gap between top plate and stage=100 mm

